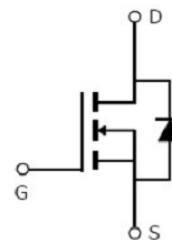


**Main Product Characteristics:**

$V_{DSS}$	600V
$R_{DS(on)}$	0.69ohm(typ.)
$I_D$	10A


**TO220F**

**Marking and pin Assignment**

**Schematic diagram**
**Features and Benefits:**

- Advanced MOSFET process technology
- Special designed for PWM, load switching and general purpose applications
- Ultra low on-resistance with low gate charge
- Fast switching and reverse body recovery
- 150°C operating temperature


**Description:**

It utilizes the latest processing techniques to achieve the high cell density and reduces the on-resistance with high repetitive avalanche rating. These features combine to make this design an extremely efficient and reliable device for use in power switching application and a wide variety of other applications

**Absolute max Rating:**

Symbol	Parameter	Max.	Units
$I_D @ TC = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$ ①	10	A
$I_D @ TC = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$ ①	6	
$I_{DM}$	Pulsed Drain Current②	40	
$P_D @ TC = 25^\circ C$	Power Dissipation③	156	W
	Linear Derating Factor	1.2	W/°C
$V_{DS}$	Drain-Source Voltage	600	V
$V_{GS}$	Gate-to-Source Voltage	± 30	V
$E_{AS}$	Single Pulse Avalanche Energy @ L=14.2mH	700	mJ
$I_{AS}$	Avalanche Current @ L=14.2mH	10	A
$T_J T_{STG}$	Operating Junction and Storage Temperature Range	-55 to + 150	°C

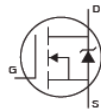
## Thermal Resistance

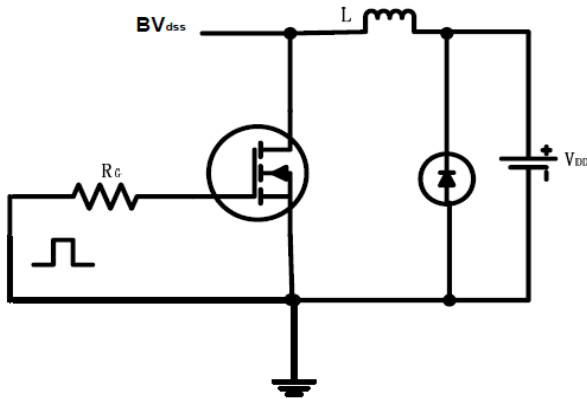
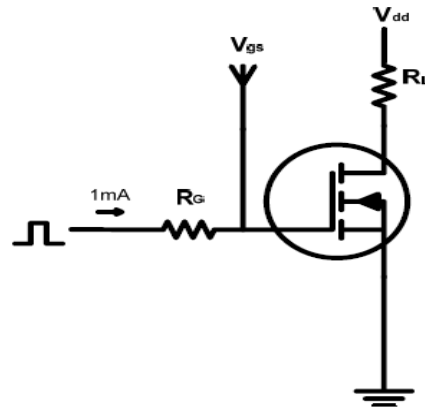
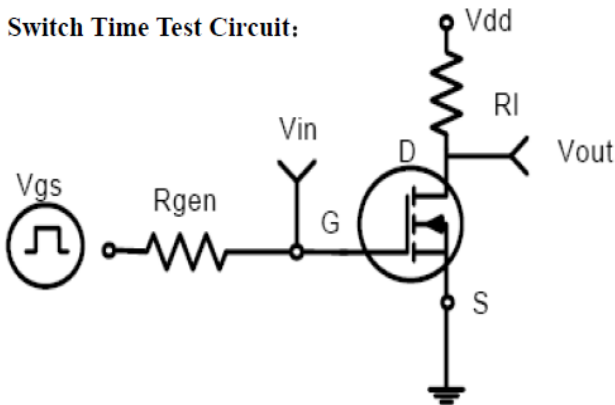
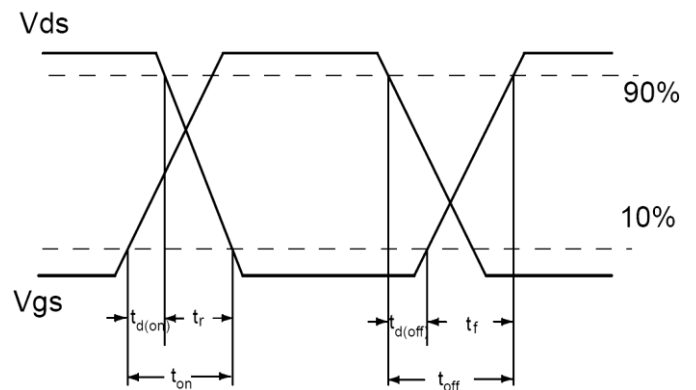
Symbol	Characterizes	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-case <sup>③</sup>	—	0.8	°C/W
$R_{\theta JA}$	Junction-to-ambient ( $t \leq 10s$ ) <sup>④</sup>	—	62	°C/W
	Junction-to-Ambient (PCB mounted, steady-state) <sup>④</sup>	—	40	°C/W

## Electrical Characterizes @ $T_A=25^\circ\text{C}$ unless otherwise specified

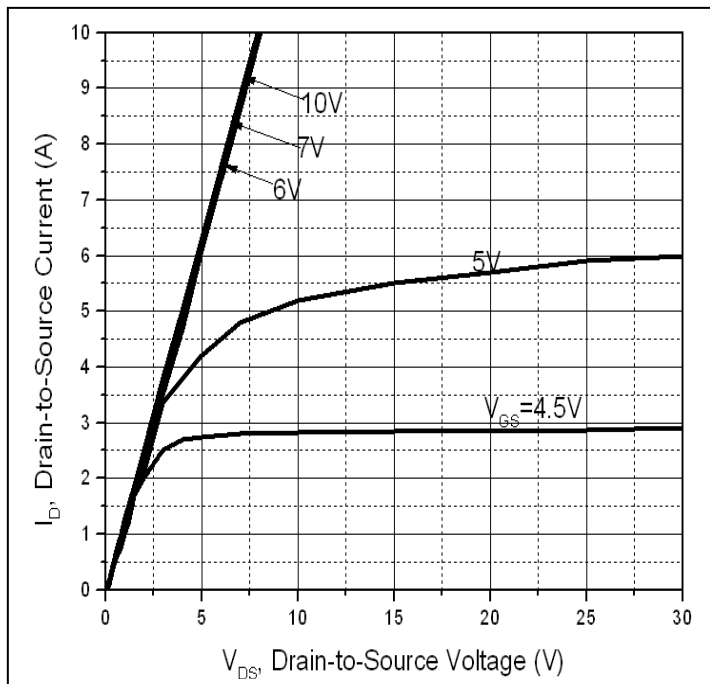
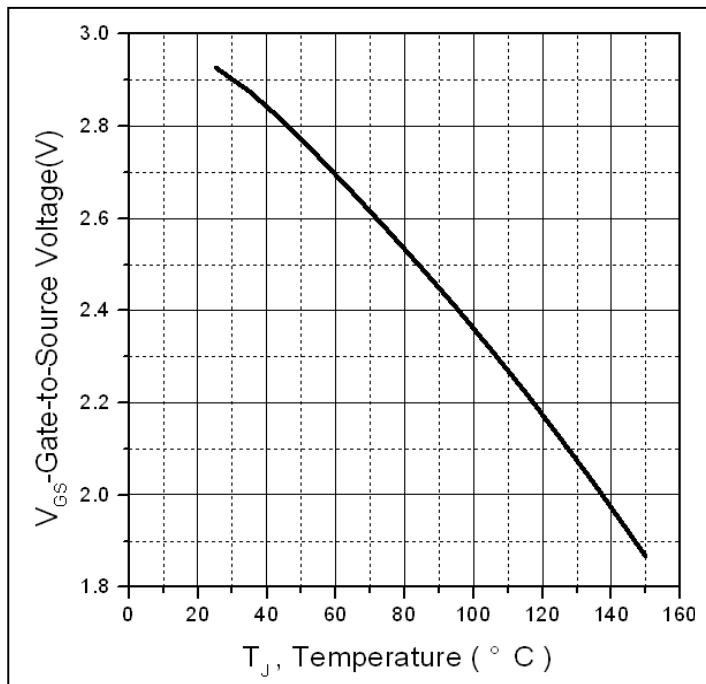
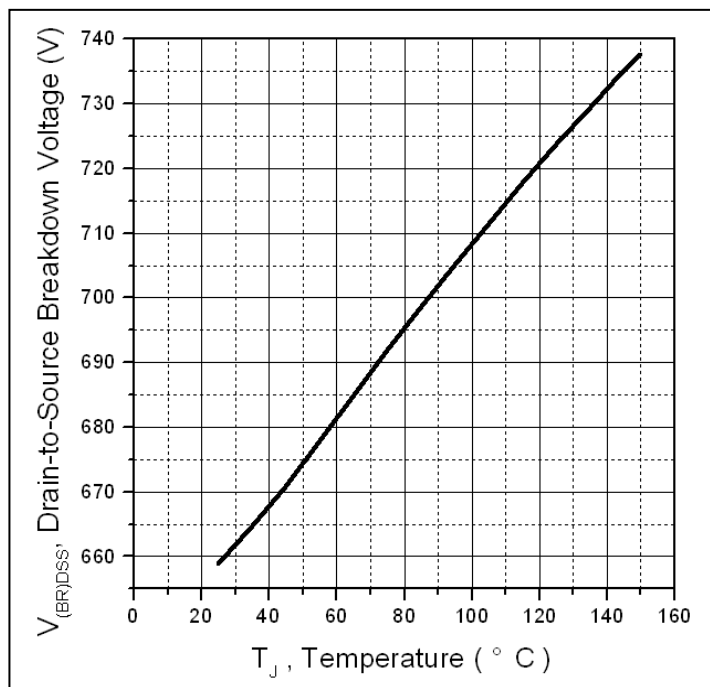
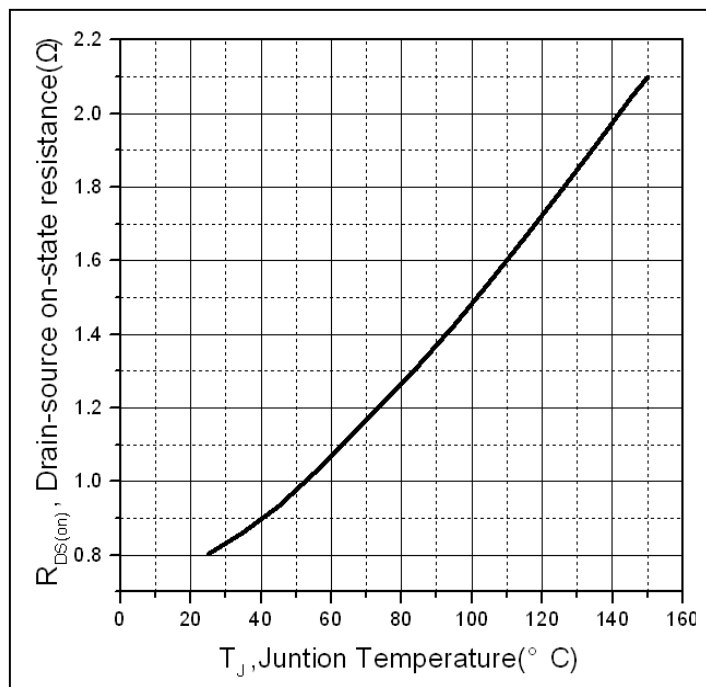
Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source breakdown voltage	600	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$R_{DS(on)}$	Static Drain-to-Source on-resistance	—	0.69	0.8	$\Omega$	$V_{GS}=10V, I_D = 5A$
		—	1.54	—		$T_J = 125^\circ\text{C}$
$V_{GS(th)}$	Gate threshold voltage	2	—	4	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
		—	2.1	—		$T_J = 125^\circ\text{C}$
$I_{DSS}$	Drain-to-Source leakage current	—	—	1	$\mu A$	$V_{DS} = 600V, V_{GS} = 0V$
		—	—	50		$T_J = 125^\circ\text{C}$
$I_{GSS}$	Gate-to-Source forward leakage	—	—	100	nA	$V_{GS} = 30V$
		—	—	-100		$V_{GS} = -30V$
$Q_g$	Total gate charge	—	42.1	—	nC	$I_D = 10A,$ $V_{DS}=480V,$ $V_{GS} = 10V$
$Q_{gs}$	Gate-to-Source charge	—	8.2	—		
$Q_{gd}$	Gate-to-Drain("Miller") charge	—	16.2	—		
$t_{d(on)}$	Turn-on delay time	—	20.9	—	ns	$V_{GS}=10V, V_{DS}=330V,$ $R_L=33\Omega,$ $R_{GEN}=25\Omega$ $I_D=10A$
$t_r$	Rise time	—	36.4	—		
$t_{d(off)}$	Turn-Off delay time	—	119.9	—		
$t_f$	Fall time	—	52.2	—		
$C_{iss}$	Input capacitance	—	1515	—	pF	$V_{GS} = 0V$
$C_{oss}$	Output capacitance	—	137	—		$V_{DS} = 25V$
$C_{riss}$	Reverse transfer capacitance	—	9	—		$f = 1MHz$

## Source-Drain Ratings and Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$I_S$	Continuous Source Current (Body Diode)	—	—	10	A	MOSFET symbol showing the integral reverse p-n junction diode. 
$I_{SM}$	Pulsed Source Current (Body Diode)	—	—	40	A	
$V_{SD}$	Diode Forward Voltage	—	0.90	1.3	V	$I_S=10A, V_{GS}=0V$
$t_{rr}$	Reverse Recovery Time	—	866	—	ns	$T_J = 25^\circ\text{C}, I_F = 10A,$
$Q_{rr}$	Reverse Recovery Charge	—	5163	—	nC	$di/dt = 100A/\mu s$

**Test circuits and Waveforms**
**EAS test circuits:**

**Gate charge test circuit:**

**Switch Time Test Circuit:**

**Switch Waveforms:**

**Notes:**

- ① Calculated continuous current based on maximum allowable junction temperature.
- ② Repetitive rating; pulse width limited by max. junction temperature.
- ③ The power dissipation PD is based on max. junction temperature, using junction-to-case thermal resistance.
- ④ The value of  $R_{\theta JA}$  is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with  $T_A = 25^\circ C$

**Typical electrical and thermal characteristics**

**Figure 1: Typical Output Characteristics**

**Figure 2. Gate to source cut-off voltage**

**Figure 3. Drain-to-Source Breakdown Voltage vs. Temperature**

**Figure 4: Normalized On-Resistance Vs. Case Temperature**

Typical electrical and thermal characteristics

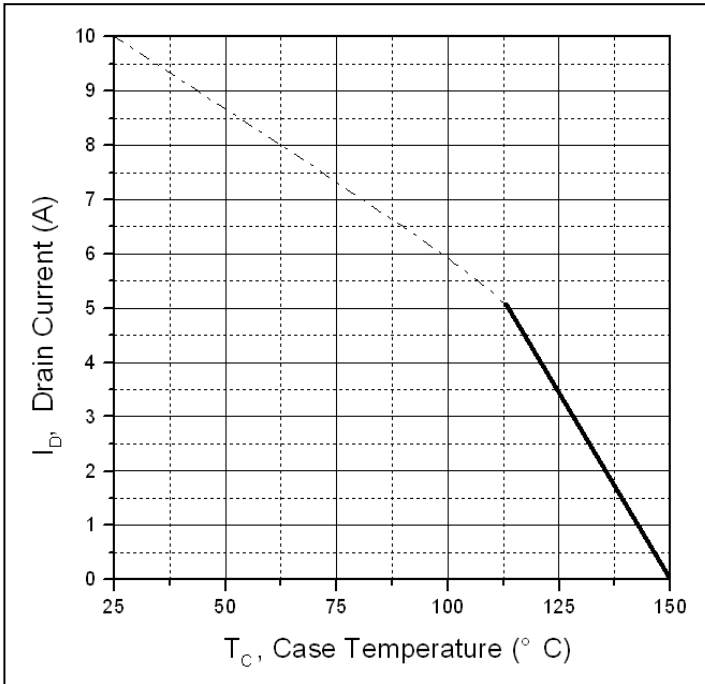


Figure 5. Maximum Drain Current Vs. Case Temperature

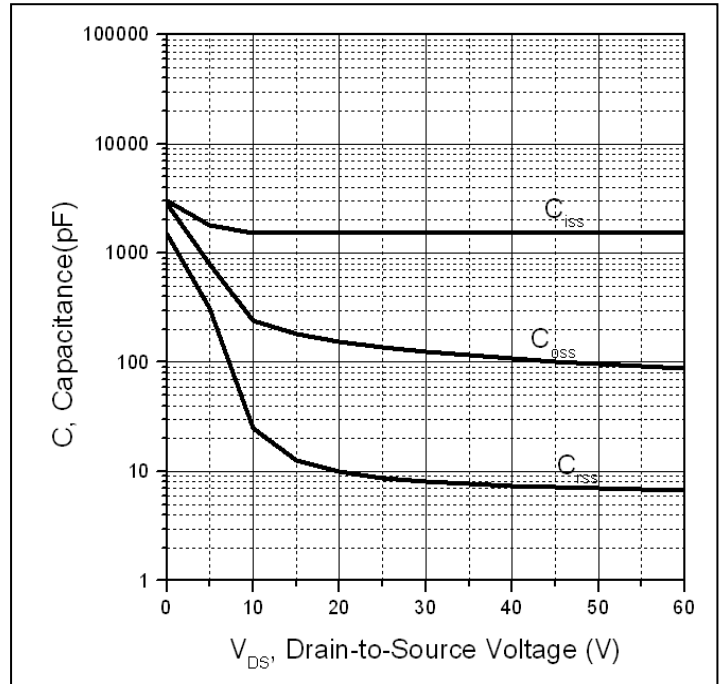


Figure 6. Typical Capacitance Vs. Drain-to-Source Voltage

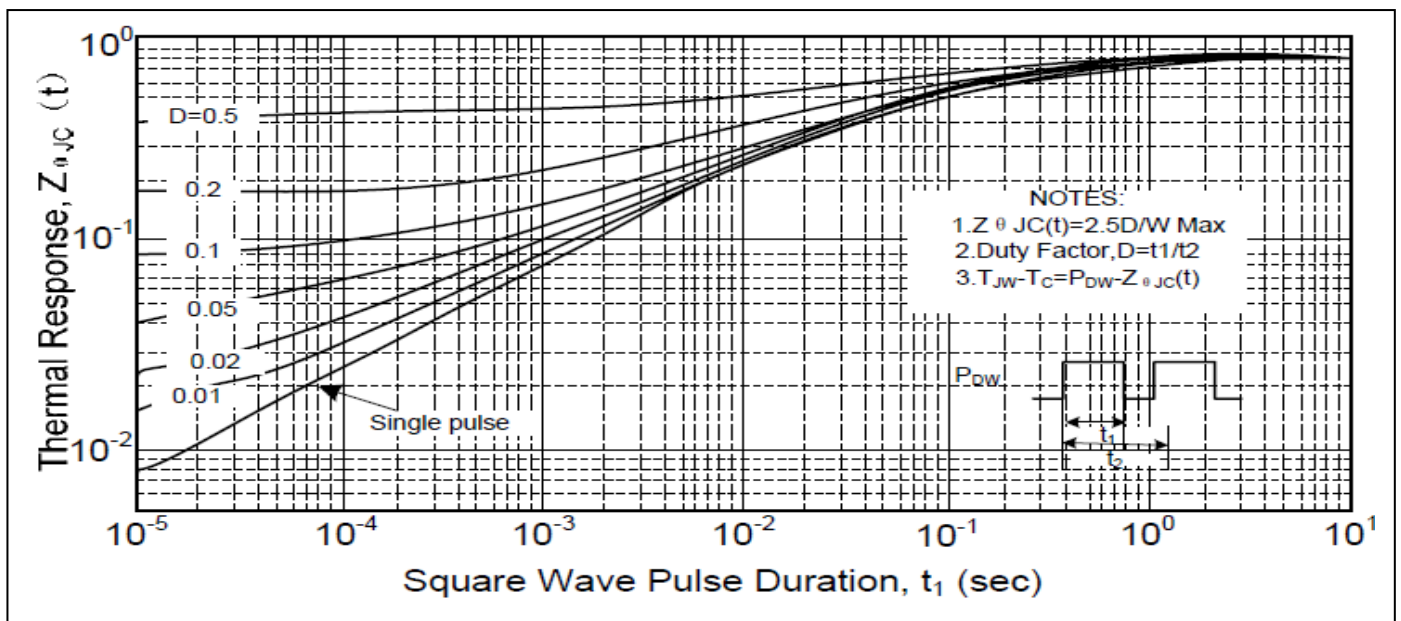
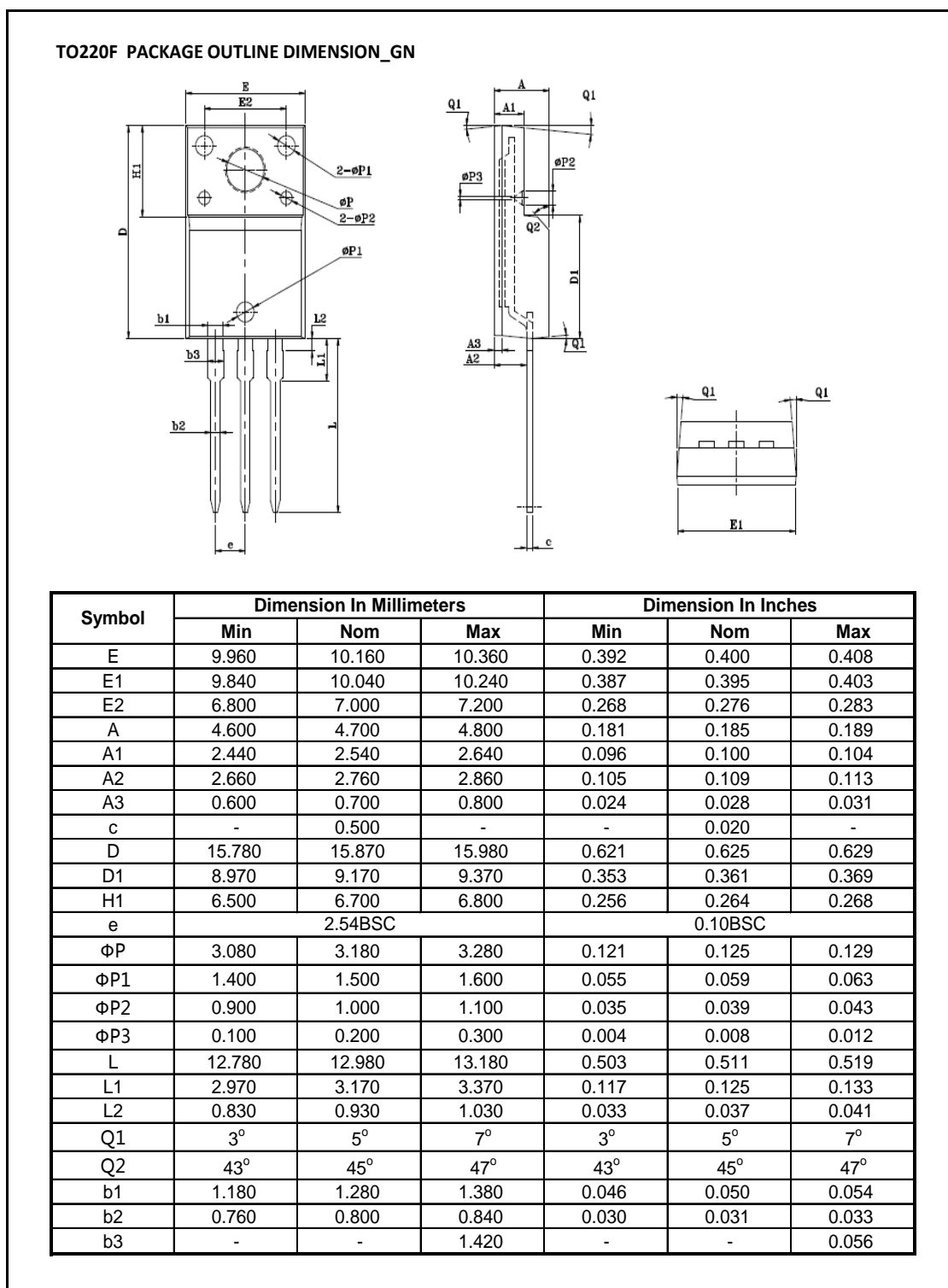


Figure 7. Maximum Effective Transient Thermal Impedance, Junction-to-Case

**Mechanical Data:**


**Ordering and Marking Information**
**Device Marking: SSF10N60F**

**Package (Available)**  
**TO220F**  
**Operating Temperature Range**  
**C : -55 to 150 °C**

**Devices per Unit**

Package Type	Units/Tube	Tubes/Inner Box	Units/Inner Box	Inner Boxes/Carton Box	Units/Carton Box
TO220F	50	20	1000	6	6000

**Reliability Test Program**

Test Item	Conditions	Duration	Sample Size
High Temperature Reverse Bias(HTRB)	T <sub>j</sub> =125°C to 150°C @ 80% of Max V <sub>DSS</sub> /V <sub>CES</sub> /V <sub>R</sub>	168 hours 500 hours 1000 hours	3 lots x 77 devices
High Temperature Gate Bias(HTGB)	T <sub>j</sub> =150°C @ 100% of Max V <sub>GSS</sub>	168 hours 500 hours 1000 hours	3 lots x 77 devices

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